

REMARKS/ARGUMENTS

Claims 23-28, 30, 31, and 33-57 are pending in this application. By this Amendment, Applicant amends Claims 30, 31, 34-36, and 49-51.

Claims 23-28, 30, 31, and 33-57 were rejected under 35 U.S.C. §112, second paragraph, for allegedly being indefinite. Particularly, the Examiner alleged, "the language 'properties of the boundary acoustic wave device are not changed by changes in surface conditions of the single crystal substrate and the solid layer' is unclear as it is not clear what properties are not changed, and it is unclear what conditions are changed." Applicant has amended Claims 31 and 34 to remove this recitation. Accordingly, Applicant respectfully requests reconsideration and withdrawal of this rejection.

Claims 23-28, 31, 33, 35-38, and 41 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. (US 2002/0158549) in view of Taniguchi (U.S. 2001/0008387), Takayama et al. (U.S. 2004/0174233), and Nishiyama et al. (U.S. 2007/0132339). Claim 30 was rejected under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., and Nishiyama et al., and further in view of Takamine (U.S. 2002/0135267). Claims 34, 43-48, and 50 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., and Nakahata et al. (U.S. 6,025,636). Claims 39 and 40 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., and Nishiyama et al., and further in view of Mishima et al. (U.S. 2005/0099091). Claim 42 was rejected under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., and Nishiyama et al., and further in view of Kadota et al. (U.S. 5,260,913). Claim 49 was rejected under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., and Nakahata et al., and further in view of Takamine. Claims 51-53 and 56 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., Nakahata et al., and Nishiyama et al. Claims 54

and 55 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., Nakahata et al., Nishiyama et al., and Mishima et al. Claim 57 was rejected under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., Nakahata et al., and Kadota et al. Applicant respectfully traverses the rejections of claims 23-28, 30, 31, and 33-57.

Claim 31 has been amended to recite:

A boundary acoustic wave device using a non-leaky propagation type boundary acoustic wave, comprising:
a plurality of boundary acoustic wave elements, each boundary acoustic wave element including a single crystal substrate, a solid layer provided on the single crystal substrate, and interdigital electrodes arranged at a boundary between the single crystal substrate and the solid layer; wherein
the single crystal substrates have a same cut angle;
a propagation direction of a boundary acoustic wave of at least one of the boundary acoustic wave elements is different from that of at least one of the other boundary acoustic wave elements;
energy of the boundary acoustic wave is not present on an outer surface of the single crystal substrate and is not present on an outer surface of the solid layer;
a thickness of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate;
 $H/\lambda > 8261.744\rho^{-1.376}$, when ρ (kg/m^3) represents the density of the electrodes, H represents the thickness of the electrodes, and λ represents the wavelength of a boundary wave which is defined by a placement period of electrode fingers of the interdigital electrodes;
and
 $\rho > 3,745 \text{ kg/m}^3$. (emphasis added)

Claim 34 has been amended to recite:

A boundary acoustic wave device using a non-leaky propagation type boundary acoustic wave, comprising:
a plurality of boundary acoustic wave elements, each boundary acoustic wave element including a single crystal substrate, a solid layer provided on the single crystal substrate, and interdigital

electrodes arranged at a boundary between the single crystal substrate and the solid layer; wherein

the single crystal substrates have a same cut angle;

a propagation direction of a boundary acoustic wave of at least one of the boundary acoustic wave elements is different from that of at least one of the other boundary acoustic wave elements;

energy of the boundary acoustic wave is not present on an outer surface of the single crystal substrate and is not present on an outer surface of the solid layer;

a thickness of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate; and the piezoelectric single crystal substrate is a LiNbO₃ substrate, ϕ of Euler angles (ϕ , θ , ψ) of the LiNbO₃ substrate is in the range of -

31° to 31°, and θ and ψ are in the range surrounded by points A1 to A13 shown in the following Table 1:

Table 1

Points	ϕ (°)	θ (°)
A01	0	116
A02	11	118
A03	20	123
A04	25	127
A05	33	140
A06	60	140
A07	65	132
A08	54	112
A09	48	90
A10	43	87
A11	24	90
A12	0	91
A13	0	116

. (emphasis added)

The Examiner alleged that the combination of Itakura et al., Taniguchi, Takayama et al., and Nishiyama et al. teaches all of the features recited in Applicant's Claim 31, and that the combination of Itakura et al., Taniguchi, Takayama et al., and Nakahata teaches all of the features recited in Applicant's Claim 34. The Examiner

acknowledged that neither Itakura et al. nor Taniguchi teaches or suggests that the thickness of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate. The Examiner alleged that Takayama et al. teaches this feature. Thus, the Examiner concluded that it would have been obvious "to combine the electrode thickness of Takayama et al. with the boundary acoustic wave device of Itakura et al. as modified by Taniguchi for the benefit of reducing the propagation loss." Applicant respectfully disagrees.

Contrary to the Examiner's allegations, none of Itakura et al., Taniguchi, Takayama et al., Nishiyama et al., and Nakahata et al. teach or suggest any boundary acoustic wave devices whatsoever. To the contrary, each of Itakura et al., Taniguchi, Takayama et al., and Nakahata et al. discloses only surface acoustic wave devices. Thus, Itakura et al., Taniguchi, Takayama et al., Nishiyama et al., and Nakahata et al. clearly fail to teach or suggest the features of "a plurality of boundary acoustic wave elements, each boundary acoustic wave element including a single crystal substrate, a solid layer provided on the single crystal substrate, and electrodes arranged at a boundary between the single crystal substrate and the solid layer" and "energy of the boundary acoustic wave is not present on an outer surface of the single crystal substrate and is not present on an outer surface of the solid layer" as recited in Applicant's Claims 31 and 34.

In paragraph 38 of the Response to Arguments section on page 16 of the outstanding Office Action, the Examiner again alleged, "[B]oth Itakura et al. and Nakahata et al. disclose boundary acoustic wave devices, as can be seen in figure 1 of Itakura et al. and at least figure 40 of Nakahata et al." This is absolutely incorrect and unsupported by any evidence of record.

As noted above, Itakura et al. and Nakahata et al. specifically disclose a surface acoustic wave device and fail to teach or suggest anything at all about a boundary

acoustic wave device. For some unknown reason, contrary to the clear and explicit teachings of Itakura et al. and Nakahata et al., the Examiner continues to allege that Itakura et al. and Nakahata et al. teach boundary acoustic wave devices.

The Examiner appears to be under the erroneous impression that any acoustic wave device that includes a piezoelectric layer and another solid layer with an electrode disposed therebetween is necessarily a boundary acoustic wave device. This is clearly incorrect.

As the Examiner should be aware, a boundary acoustic wave device, by definition and as is well known by those of ordinary skill in the art, includes a piezoelectric substrate, a solid layer provided on the piezoelectric substrate and an electrode arranged at a boundary between the single crystal substrate and the solid layer, and constructed such that an acoustic energy is concentrated at the boundary between the single crystal substrate and the solid layer. Because no significant amount of energy is concentrated on the surface of either of the solid layers, a propagation of the boundary wave is not effected by a change in the surface condition of the solid layers. In order for the acoustic wave device including the structural elements described above to function as a boundary acoustic wave device, the thickness of the solid layer must be set to a specific value which enables the acoustic energy to be concentrated at the boundary between the single crystal substrate and the solid layer. With other thicknesses of the solid layer (usually smaller thicknesses), the acoustic wave device will function as a surface acoustic wave device, such as the devices of Itakura et al. and Nakahata et al., not as a boundary acoustic wave device.

Although Applicant respectfully disagrees with the prior art rejections of Applicant's Claims 23-28, 30, 31, and 33-57, in order to advance prosecution and more clearly define the boundary acoustic wave device of the present invention, as noted above, Applicant has amended Claims 31 and 34 to recite the feature of "energy of the boundary acoustic wave is not present on an outer surface of the single crystal substrate and is not present on an outer surface of the solid layer." Support for this

feature is found in paragraph [0006] of Applicant's originally filed Substitute Specification.

Neither Itakura et al. nor Nakahata et al. teaches or suggests the feature of "energy of the boundary acoustic wave is not present on an outer surface of the single crystal substrate and is not present on an outer surface of the solid layer" as recited in Applicant's Claims 31 and 34. In fact, since the devices disclosed in Itakura et al. and Nakahata et al. are surface acoustic wave devices, not boundary acoustic wave devices, the energy of the acoustic wave of each of Itakura et al. and Nakahata et al., would necessarily be present on at least one of an outer surface of a single crystal substrate and an outer surface of a solid layer. Thus, Itakura et al. and Nakahata et al. certainly fail to teach or suggest the feature of "energy of the boundary acoustic wave is not present on an outer surface of the single crystal substrate and is not present on an outer surface of the solid layer" as recited in Applicant's Claims 31 and 34.

Applicant respectfully requests that the Examiner explain where in Itakura et al. or Nakahata et al. a boundary acoustic wave device is disclosed, or where Itakura et al. or Nakahata et al. teaches or suggests that the devices disclosed therein function as boundary acoustic wave devices or excite any boundary acoustic waves.

Applicant notes that the Examiner has failed to address or respond to Applicant's arguments regarding specifically why neither Itakura et al. nor Nakahata et al. teaches or suggests any boundary acoustic wave devices. Applicant respectfully requests that the Examiner specifically address and reply to the arguments presented above.

In addition, the Examiner alleged that paragraphs 8 and 83 of Takayama et al. teach the feature of "a thickness of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate" as recited in Applicant's Claims 31 and 34. However, paragraphs 8 and 83 of Takayama et al. disclose:

To overcome this problem, use of a substrate with a larger cut-angle is effective for substantial reduction of propagation loss. This idea is disclosed in Japanese Patent Application Non-Examined Publication No. H09-167936. According to this publication, the cut-angle of the substrate, which minimizes the propagation loss of the LSAW propagating on the LT single-crystal and LN single-crystal, varies in response to normalized film-thickness h/λ of the IDT electrode, where h =film thickness of the electrode, and λ =wavelength of the SAW. In the case of the LT single-crystal, when the film thickness of the IDT electrode becomes 0.03-0.15 of the wavelength of the LSAW (normalized film thickness h/λ is 3%-15%), a shift of the cut-angle from 36° to 39°-46° can almost eliminate the propagation loss. In the same manner, in the case of the LN single-crystal, when the film thickness of the IDT electrode becomes 0.03-0.15 of the wavelength of the LSAW (normalized film thickness h/λ is 3%-15%), a shift of the cut-angle from 64° to a greater angle, such as 66°-74°, can reduce the propagation loss to almost 0 (zero).

...

A saw resonator as comparison sample 1 has the following specifications: pitch "p" of finger-electrodes 301 is 1.06 μm , and normalized film thickness h/λ is 6.0%. Another SAW resonator as comparison sample 2 has the following specifications: pitch "p" of finger-electrodes 301 is 1.0 μm , and normalized film thickness h/λ is 11%. Those samples have resonance frequencies of 1886.0 MHz (comparison sample 1) and 1884.9 MHz (comparison sample 2). The acoustic velocities of those comparison samples can be found by equation (1) and with their resonance frequencies f , comparison sample 1 has an acoustic velocity of 3998.3 m/s, and comparison sample 2 has an acoustic velocity of 3769.8 m/s. Those velocities are faster than the phase velocity of the slow shear wave propagating on the 39° Y-XLT substrate used in this first embodiment. On top of that, both of those two comparison samples do not satisfy the relation of $2xp \leq vb/f$.

Neither these portions nor any other portion of Takayama et al. teach or suggest anything at all about an acoustic velocity of an **SH type boundary acoustic wave** relative to acoustic velocities of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate. In fact, as noted above, Takayama et al. is not even directed to a **boundary acoustic wave** device. Instead, Takayama et al. is

specifically and exclusively directed to a surface acoustic wave device, **NOT a boundary acoustic wave** device, and Takayama et al. neither teaches or suggests that the structure disclosed therein could or should be used for a boundary acoustic wave device.

At best, paragraphs [0008] and [0082] of Takayama et al. merely teaches that the phase velocity of a surface acoustic wave resonator is slower than the phase velocity vb of a slow shear wave on the LiTaO_3 . The relationship $2\pi p \leq vb/f$ disclosed in paragraph [0082] of Takayama et al. clearly does not teach or suggest the relationship of the acoustic velocities recited in Applicant's Claims 31 and 34.

Thus, contrary to the Examiner's allegations, Takayama et al. clearly fails to teach or suggest the feature of "a thickness of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate" as recited in Applicant's Claims 31 and 34.

In paragraph 43 of the outstanding Office Action, the Examiner stated, "Applicant argues that the amended claim language provides a definition of λ that is directed to the wavelength of the device, such that the applied art does not disclose the feature $H/\lambda > 8261.744\rho^{-1.376}$. However, the claim language still does not make clear what the frequency of the device is. A boundary acoustic wave [device] can excite an acoustic wave at any frequency with varying efficiency. Without a clear definition of which frequency 'the wavelength of the device' refers to, the claim as currently written can still read on any wavelength."

Although Applicant respectfully disagrees with the Examiner's allegations, Applicant's Claim 31 has been amended to recite the feature of " $H/\lambda > 8261.744\rho^{-1.376}$, when ρ (kg/m^3) represents the density of the electrodes, H represents the thickness of the electrodes, and λ represents the wavelength of a boundary wave which is defined by a placement period of electrode fingers of the interdigital electrodes." Support

for this feature is found, for example, in paragraphs [0148] and [0164] of Applicant's originally filed Substitute Specification. Thus, Applicant's Claim 31, as amended, clearly recites a feature directed to the wavelength of the device.

Since Taniguchi fails to teach or suggest any specific thickness of the IDT electrodes or any specific placement period of the electrode fingers of the IDT electrodes, contrary to the Examiner's allegation, Taniguchi certainly fails to teach or suggest the feature of " $H/\lambda > 8261.744\rho^{-1.376}$ ", when ρ (kg/m^3) represents the density of the electrodes, H represents the thickness of the electrodes, and λ represents the wavelength of a boundary wave which is defined by a placement period of electrode fingers of the interdigital electrodes" as recited in Applicant's Claim 31.

With respect to Claim 34, the Examiner alleged, "it would have been obvious to a person of ordinary skill in the art to combine the plurality of boundary acoustic wave elements having different propagation directions of Taniguchi, the electrode thickness of Takayama et al., and the crystal orientation of Nakahata with the boundary acoustic wave device of Itakura et al. for the benefits of allowing for different electromechanical coupling coefficients within the same device (Paragraph 58 of Taniguchi), reducing the propagation loss (Paragraph 8 of Takayama et al.), and improving the coupling coefficient (column 2, lines 29-42 of Nakahata). Applicant respectfully disagrees.

Although Nakahata et al. teaches a LiNbO_3 layer having Euler angles that produce an acoustic velocity of 8000 m/s or greater, Nakahata et al. is directed to surface acoustic wave devices, not a boundary acoustic wave device as recited in Applicant's Claim 34. The Euler angles used for a non-leaky propagation type boundary acoustic wave device are very different from the Euler angles used for a surface acoustic wave device. Nakahata et al. fails to teach or suggest anything at all about any specific Euler angles or any specific acoustic velocities of a boundary acoustic wave device.

Thus, the mere fact that Nakahata et al. teaches a LiNbO_3 layer having Euler angles that produce an acoustic velocity of 8000 m/s or greater in a surface acoustic

wave device certainly does not lead to the conclusion that Nakahata et al. teaches or suggests the Euler angles of the boundary acoustic wave device recited in Applicant's Claim 34.

An invention composed of several elements is not proved obvious merely by demonstrating that each of its elements was, independently, known in the prior art. *KSR Int'l Co. v. Teleflex Inc.*, 127 S.Ct. 1727, 1741 (2007).

Accordingly, Nakahata et al. clearly fails to teach or suggest the feature of "the piezoelectric single crystal substrate is a LiNbO_3 substrate, ϕ of Euler angles (ϕ , θ , ψ) of the LiNbO_3 substrate is in the range of -31° to 31° , and θ and ψ are in the range surrounded by points A1 to A13 shown in the following Table 1:

Table 1

Points	ψ (°)	θ (°)
A01	0	116
A02	11	118
A03	20	123
A04	25	127
A05	33	140
A06	60	140
A07	65	132
A08	54	112
A09	48	90
A10	43	87
A11	24	90
A12	0	91
A13	0	116

" as recited in Applicant's Claim 34.

In summary, since none of Itakura et al., Taniguchi, Takayama et al., Nishiyama et al., and Nakahata et al. teaches or suggests any boundary acoustic wave devices whatsoever, Itakura et al., Taniguchi, Takayama et al., Nishiyama et al., and Nakahata et al. certainly fail to teach or suggest the unique combination and arrangement of features recited in Applicant's Claims 31 and 34.

The Examiner has again made baseless allegations that at least Itakura et al.

and Nakahata et al. teach boundary acoustic wave device. However, these allegations are completely unsubstantiated by any teachings or suggestions in either of Itakura et al. or Nakahata et al. or any other evidence whatsoever. Further, Itakura et al. and Nakahata et al. clearly fail to teach or suggest the feature of "properties of the boundary acoustic wave device are not changed by changes in surface conditions of the single crystal substrate and the solid layer" as recited in Claims 31 and 34.

The Examiner is reminded that prior art rejections must be based on evidence. Graham v. John Deere Co., 383 U.S. 117 (1966). The Examiner is hereby requested to provide references to specific portions of Itakura et al. and Nakahata et al. or other evidence to support his position that Itakura et al. and Nakahata et al. teach or suggest boundary acoustic wave devices.

Accordingly, Applicant respectfully requests reconsideration and withdrawal of the rejection of Claim 31 under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. in view of Taniguchi and Takayama et al., and the rejection of Claim 34 under 35 U.S.C. § 103(a) as being unpatentable over Itakura et al. in view of Taniguchi and Takayama et al., and further in view of Nakahata.

The Examiner relied upon Takamine, Mishima et al., and Kadota et al. to allegedly cure various deficiencies of Itakura et al., Taniguchi, and Takayama et al. However, Takamine, Mishima et al. and Kadota et al. fail to teach or suggest the features of "a thickness of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate," "energy of the boundary acoustic wave is not present on an outer surface of the single crystal substrate and is not present on an outer surface of the solid layer," " $H/\lambda > 8261.744\rho^{-1.376}$ ", when ρ (kg/m^3) represents the density of the electrodes, H represents the thickness of the electrodes, and λ represents the wavelength of a boundary wave which is defined by a placement period of electrode fingers of the interdigital electrodes," and "the

piezoelectric single crystal substrate is a LiNbO_3 substrate, ϕ of Euler angles (ϕ, θ, ψ) of the LiNbO_3 substrate is in the range of -31° to 31° , and θ and ψ are in the range surrounded by points A1 to A13 shown in the following Table 1" as recited in Applicant's Claims 31 and 34. Thus, Applicant respectfully submits that Takamine, Mishima et al. and Kadota et al. fail to cure the deficiencies of Itakura et al., Taniguchi, Takayama et al., Nishiyama et al., and Nakahata et al. described above.

Accordingly, Applicant respectfully submits that Itakura et al., Taniguchi, Takayama et al., Takamine, Nishiyama et al., Nakahata et al., Mishima et al. and Kadota et al., applied alone or in combination, fail to teach or suggest the unique combination and arrangement of features recited in Applicant's Claims 31 and 34.

In view of the foregoing amendments and remarks, Applicant respectfully submits that Claims 31 and 34 are allowable. Claims 23-28, 30, 33, and 36-57 depend upon Claims 31 and 34, and are therefore allowable for at least the reasons that Claims 31 and 34 are allowable.

In view of the foregoing amendments and remarks, Applicant respectfully submits that this application is in condition for allowance. Favorable consideration and prompt allowance are solicited.

Application No. 10/596,359
June 24, 2009
Reply to the Office Action dated March 26, 2009
Page 22 of 22

The Commissioner is authorized to charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account No. 50-1353.

Respectfully submitted,

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